

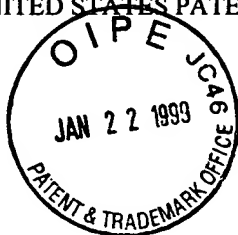
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
Mailloux, et al.

Serial No.: 08/984,562

Filed: December 3, 1997

For: MEMORY DEVICE FOR BURST OR PIPELINED
OPERATION WITH MODE SELECTION CIRCUITRY



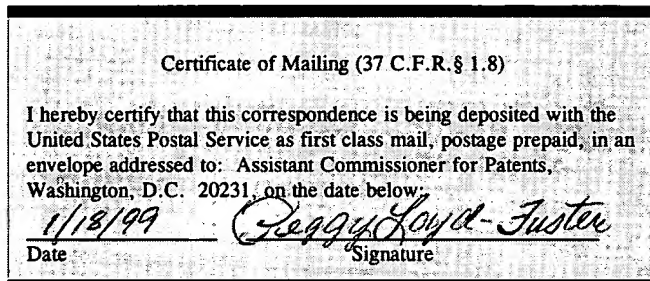
§
§ Group Art Unit: 2751
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§ Examiner: Kim, H.
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§ Atty. Docket: 95-0653.02
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INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:



In compliance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant[s] respectfully request[s] that this Information Disclosure Statement be entered and that the references listed on the attached Form PTO-1449 be considered by the Examiner and made of record. As the references are cumulative from the parent, copies of the listed references are not enclosed.

In accordance with 37 C.F.R. § 1.97(b), this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possible material information as defined in 37 C.F.R. § 1.56(a) exists.

The following references are submitted for the Examiner's review:

U.S. Patents

<u>U.S. Patent No.</u>	<u>Issue Date</u>	<u>Inventor</u>
5,357,469	10/18/94	Sommer et al.
5,268,865	12/7/93	Takasugi
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4,567,579	1/28/86	Patel et al.
4,484,308	11/20/84	Lewandowski et al.
4,875,192	10/17/89	Matsumoto
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4,562,555	12/31/85	Ouchi et al.
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Other References

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Samsung Electronics, "Samsung Synchronous DRAM", March 1993, pgs. 1-16

Oki Electric Ind. Co., Ltd., "Burst DRAM Function & Pinout", 2nd presentation, Item #619, September, 1994

Toshiba America Electronic Components, Inc., "Application Specific DRAM, 1994", Pgs. C-178, C-260, C218

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This Information disclosure Statement is being submitted after the mailing of the first Office Action, but before the mailing of a Final Rejection or Notice of Allowance. The Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) of \$240.00 and any additional fees which may be required to Micron Technology, Inc. Deposit Account No. 13-3092, Order No. 95-0653.02.

If there are any matters which may be resolved or clarified through telephone interview, the Examiner is respectfully requested to contact Applicant's undersigned attorney at the number indicated.

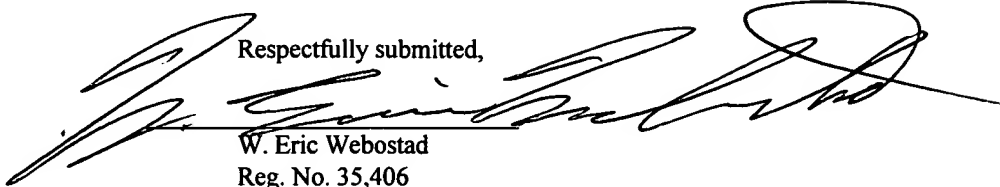
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A Form PTO-1449 is enclosed herewith.

Date:

1-18-99

Respectfully submitted,



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